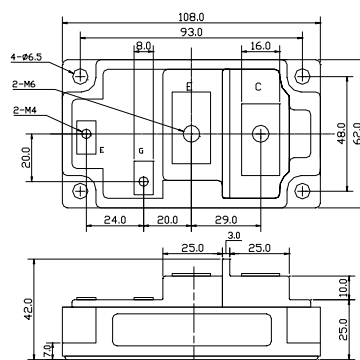
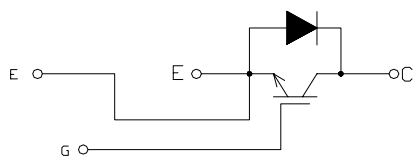


# IGBT MODULE Single 200A 1200V

# PHMB200B12

CIRCUIT

OUTLINE DRAWING



Dimension(mm)

Approximate Weight : 500g

MAXIMUM RATINGS (T<sub>C</sub>=25°C)

Item	Symbol	PHMB200B12		Unit
Collector-Emitter Voltage	V <sub>CES</sub>	1200		V
Gate - Emitter Voltage	V <sub>GES</sub>	+/- 20		V
Collector Current	I <sub>C</sub>	DC	200	A
		1 ms	400	
Collector Power Dissipation	P <sub>C</sub>	960		W
Junction Temperature Range	T <sub>j</sub>	-40 to +150		°C
Storage Temperature Range	T <sub>stg</sub>	-40 to +125		°C
Isolation Voltage Terminal to Base AC, 1 min.)	V <sub>ISO</sub>	2500		V
Mounting Torque	Module Base to Heatsink	3		N•m
	Bus Bar to Main Terminals	M4	1.4	
		M6	3	

ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Emitter Cut-Off Current	I <sub>CES</sub>	V <sub>CE</sub> =1200V, V <sub>GE</sub> =0V	-	-	4.0	mA
Gate-Emitter Leakage Current	I <sub>GES</sub>	V <sub>GE</sub> =+/- 20V, V <sub>CE</sub> =0V	-	-	1.0	μA
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =200A, V <sub>GE</sub> =15V	-	1.9	2.4	V
Gate-Emitter Threshold Voltage	V <sub>GE(th)</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =200mA	4.0	-	8.0	V
Input Capacitance	C <sub>ies</sub>	V <sub>CE</sub> =10V, V <sub>GE</sub> =0V, f=1MHz	-	16600	-	pF
Switching Time	Rise Time	V <sub>CC</sub> = 600V R <sub>L</sub> = 3 ohm R <sub>G</sub> = 2 ohm V <sub>GE</sub> = +/- 15V	-	0.25	0.45	μs
	Turn-on Time		-	0.40	0.70	
	Fall Time		-	0.25	0.35	
	Turn-off Time		-	0.80	1.10	

FREE WHEELING DIODES RATINGS & CHARACTERISTICS (T<sub>C</sub>=25°C)

Item	Symbol	Rated Value		Unit
Forward Current	I <sub>F</sub>	DC	200	A
		1 ms	400	

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Peak Forward Voltage	V <sub>F</sub>	I <sub>F</sub> =200A, V <sub>GE</sub> =0V	-	1.9	2.4	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =200A, V <sub>GE</sub> =-10V, di/dt=400A/μs	-	0.2	0.3	μs

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Thermal Impedance	IGBT	Junction to Case	-	-	0.125	°C/W
	DIODE		-	-	0.24	

# PHMB200B12

Fig.1- Output Characteristics (Typical)

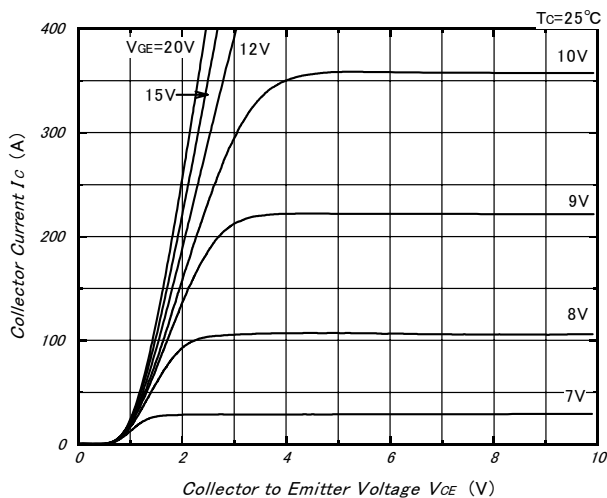


Fig.2- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

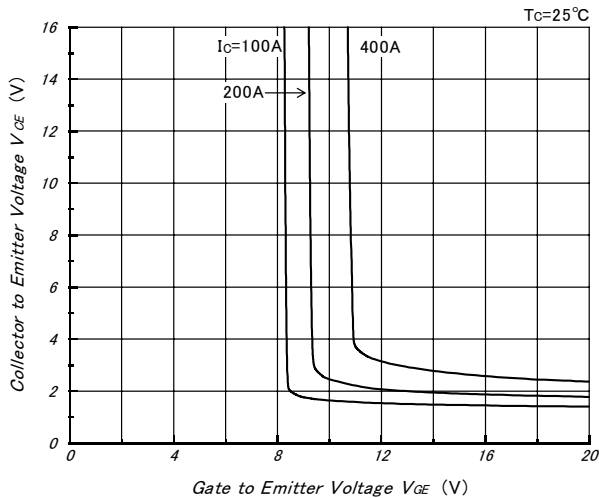


Fig.3- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

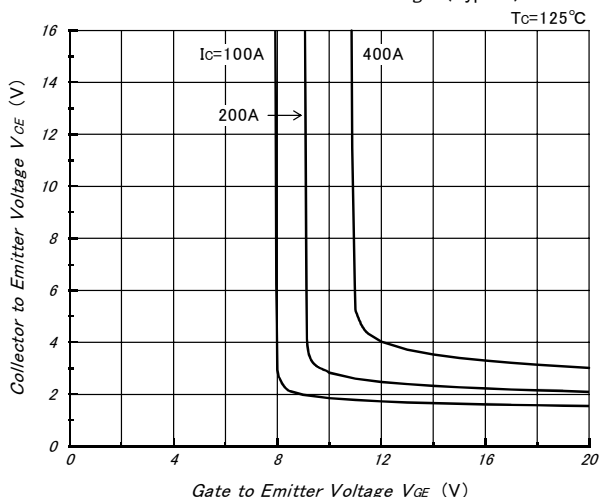


Fig.4- Gate Charge vs. Collector to Emitter Voltage (Typical)

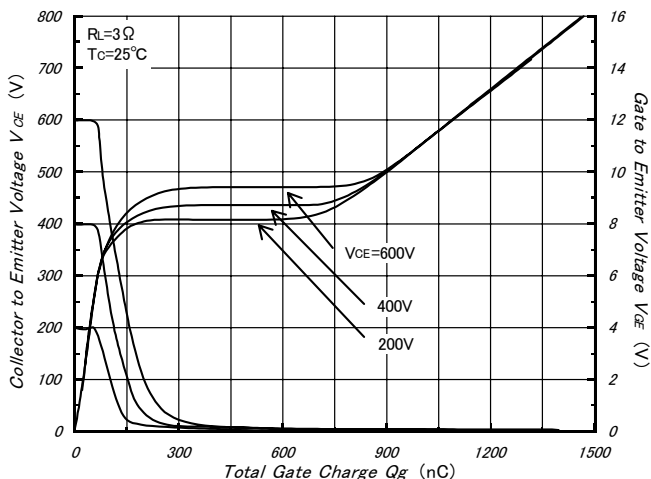


Fig.5- Capacitance vs. Collector to Emitter Voltage (Typical)

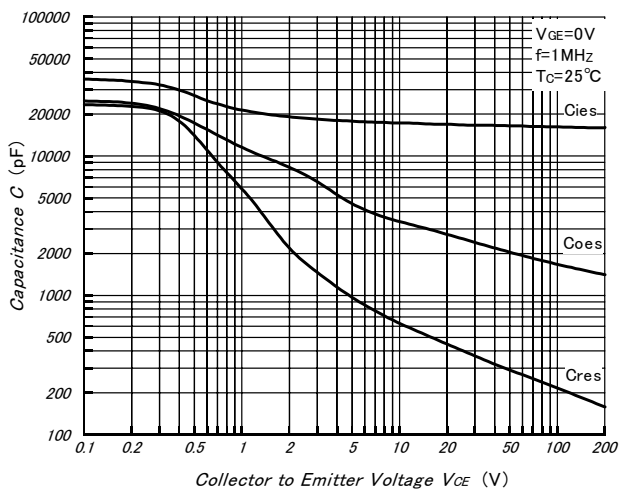
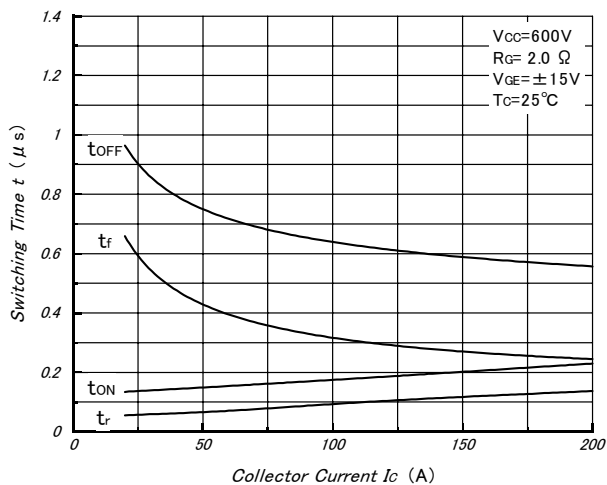


Fig.6- Collector Current vs. Switching Time (Typical)



# PHMB200B12

Fig.7- Series Gate Impedance vs. Switching Time (Typical)

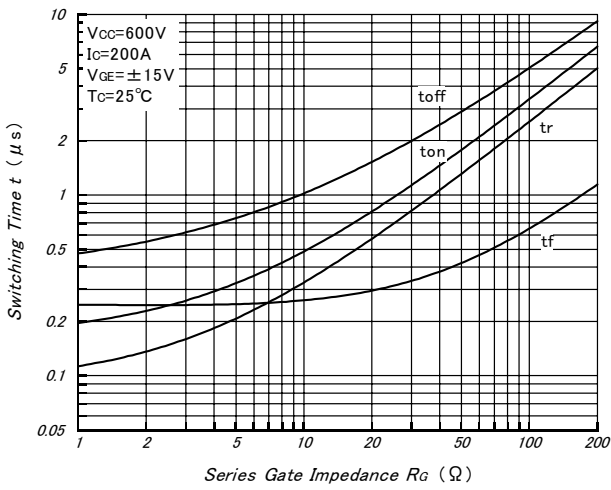


Fig.8- Forward Characteristics of Free Wheeling Diode (Typical)

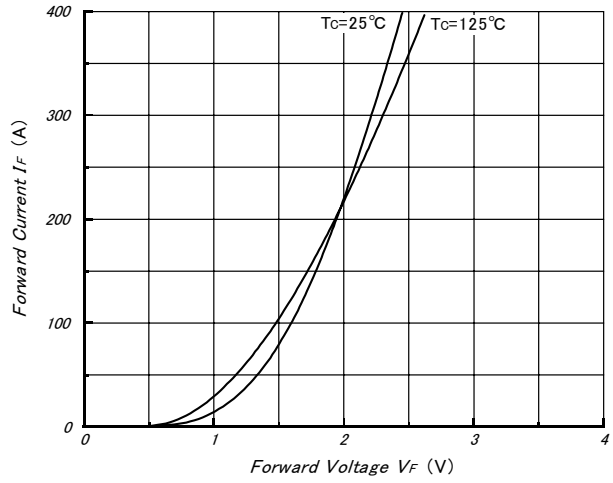


Fig.9- Reverse Recovery Characteristics (Typical)

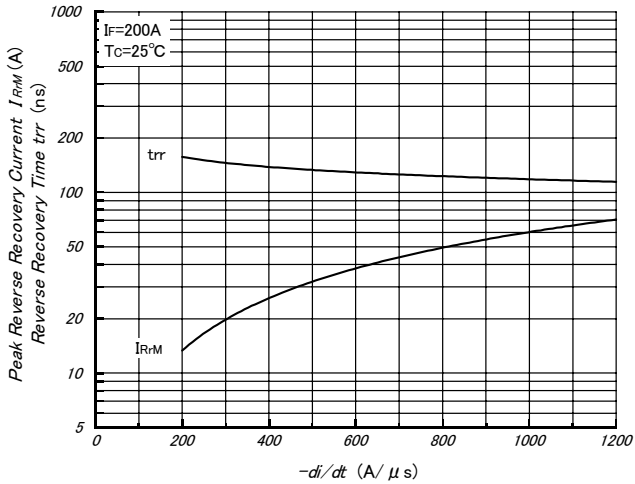


Fig.10- Reverse Bias Safe Operating Area (Typical)

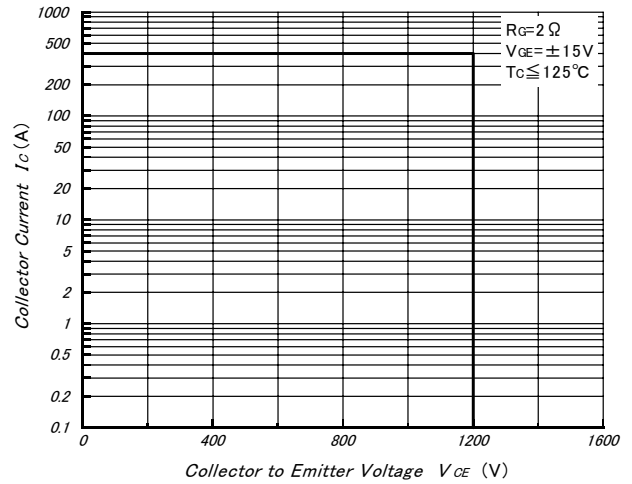


Fig.11- Transient Thermal Impedance

